

Impedance Spectra of Mixed Conductors: a 2D Study of Ceria

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Abstract

In this paper we develop an analytical framework for the study of electrochemical impedance of mixed ionic and electronic conductors (MIEC). The framework is based on first-principles and it features the coupling of electrochemical reactions, surface transport and bulk transport processes. We utilize this work to analyze two-dimensional systems relevant for fuel cell science via finite element method (FEM). Alternate Current Impedance Spectroscopy (AC-IS or IS) of a ceria symmetric cell is simulated near equilibrium condition (zero bias) for a wide array of working conditions including variations of temperature and H_2 partial pressure on a two-dimensional fuel cell sample with patterned metal electrodes. The model shows agreement of IS curves with the experimental literature with the relative error on the impedance being consistently below 2%. Important two-dimensional effects such as the effects of thickness decrease and the influence of variable electronic and ionic diffusivities on the impedance spectra are also explored.

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1 I. INTRODUCTION

2 Mixed ionic and electronic conductors (MIEC), or in short mixed conductors, are sub-
3 stances capable of conducting both electrons and ions, and for that reason they are used
4 in many applications and most notably in catalysis and eletrochemistry: they have been
5 employed in gas sensors, fuel cells, oxygen permeation membranes, oxygen pumps and elec-
6 trolyzers.

7 The study of the alternate current properties of MIEC aides in understanding many of
8 the physical chemical phenomena related to the behavior of defects, electrochemistry and
9 interfaces. A technique frequently used to probe the interplay between these processes
10 is impedance spectroscopy (IS). IS consists in injecting a "small" sinusoidal current into
11 an electrochemical sample, a fuel cell for example, which is initially under steady-state
12 conditions. This perturbation in turn induces a small sinusoidal and de-phased perturbation
13 of the voltage. From the measurements of voltage and current over a wide set of frequencies,
14 one can compute the complex impedance of the system. When the experiment is compared
15 against a suitable model, impedance spectroscopy helps understand the linear physics of
16 electro-active materials.

17 The tools used to deconvolute impedance spectra and relate them to physical-chemical
18 quantities are usually limited to one-dimensional equivalent circuits ([1] and [2]). Even
19 though the 1D approach is very useful because it enables the comparison of different pro-
20 cesses, it sometimes fails to help interpret satisfactorily physical chemical phenomena that
21 extend to several dimensions. Only a handful of works attempted to scale up to two dimen-
22 sions, and generally have been constrained to the steady-state setting [3] [4] and [5].

23 In this paper we develop a fast method for the computation of impedance spectra for
24 highly-doped mixed conductors in a 2D setting under geometrically symmetric conditions.
25 The system studied was chosen so that it is not too cumbersome algebraically and readily
26 relatable to experiments. However the methodology is general and it can be extended easily
27 to 3D, to dissymmetric systems under non-zero bias and to complex chemical boundary
28 conditions.

29 The paper proceeds as follows: we first develop a model for impedance spectroscopy and
30 determine the impedance equations [6], then we compare our results to experimental data,
31 finally we study the influence of parameter variation on the IS: the thickness of the sample,

1 the rates of the chemical reactions at the exposed MIEC surface and the diffusivity profiles.

2 After non-dimensionalization of the full drift diffusion equations, we find that the ratio
3 between the Debye length and the characteristic length scale of the material is remarkably
4 large, hence we singularly perturb the governing equations and we deduce that electroneu-
5 trality is satisfied for a large portion of the sample. Then we apply a small sinusoidal
6 perturbation to the potential, which mathematically translates into a regular perturbation
7 of the equations; after formal algebraic manipulations we collect first order terms and de-
8 duce two complex and linear partial differential equations in 2D space and time. Thank to
9 linearity, the Fourier transformation of these equations and their boundary conditions leads
10 to the determination of the complex impedance spectroscopy equations which we solve in
11 2D space for the frequencies of interest.

12 We verify our numerical results against experiments that are relevant for fuel cell appli-
13 cations. In particular, we study the case of a Samarium Doped Ceria (SDC) cell, immersed
14 in a uniform atmosphere of argon, hydrogen and water vapor. The cell is symmetric and
15 reversible and has been subject of extensive research [7] [8] and [9]. We find excellent agree-
16 ment between the computed impedance spectra and experimental data. This shows that
17 the approximations and the model are likely to be valid, hence this framework could help
18 address a number of important fundamental physical/chemical issues in mixed conductors.

19 II. SYSTEM UNDER STUDY

20 The physical system under study is a two-dimensional assembly which consists of a mixed
21 oxygen ion and electron conductor slab of thickness $2l_2$ sandwiched between two identical
22 patterned metal current collectors, Fig 1. The patterned collectors are repeated and sym-
23 metrical with respect to the center line Γ_1 . Hence the system to be reduced to a repeating
24 cell using the mirror symmetry lines Γ_1 , Γ_2 and Γ_3 . All sides of the sample are placed in
25 a uniform gas environment. Two charge-carrying species are considered: oxygen vacancies,
26 denoted by the subscript ion, and electrons, denoted by eon.

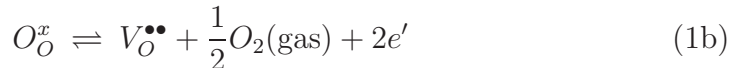
27 The framework we propose is very broad in scope, however we specialize our study to
28 Samarium Doped Ceria (SDC). Doped ceria is a class of materials that has recently gained
29 prominent relevance in fuel cell technology ([10] and [11]). We suppose that the uniform
30 gas environment consists of mixture of hydrogen, water vapor and a noble gas and we

1 solve the electrochemical potential and current of both charge carriers using a linear and
 2 time-independent model, which we develop via perturbation techniques and Fourier trans-
 3 formation. We mainly compare our computational work to the data of [8] but we also
 4 leverage on some results of [7] to justify the boundary conditions. Both works study SDC-
 5 15 (15% samarium doping), hence the background dopant particles per unit volume, B , is
 6 well defined and reported in Tab. I.

7 The surface dimensions are kept constant: the width of the metal | ceria interface (Γ_4) is
 8 $2W_1 = 3\mu m$ and the width of the gas | ceria interface (Γ_5) is $2W_2 = 5\mu m$. The thickness of
 9 the MIEC is set to be $2l_2 = 1mm$, unless otherwise specified. Due to high electronic mobility
 10 in the metal, the thickness of the metal stripe does not affect to the calculation, and thus
 11 the thickness of the electrolyte is in effect the thickness of the cell. Hence we assume that
 12 the characteristic length scale of the sample under study is $l_c = 10\mu m$. The data mentioned
 13 above is summarized in Tab. I.

14 The assumptions of the model are rather standard for MIEC. We set that the gas |
 15 metal | ceria interface, or triple-phase boundary, has a negligible contribution compared to
 16 surface reactions [12]. We further treat the surface chemistry as one global reaction, and
 17 do not consider diffusion of adsorbed species on the surface [13]. Combined with the final
 18 assumption that the metal | ceria interface is reversible to electrons, i.e., a Ohmic condition,
 19 [3], we are only considering two steps in the electrode reaction pathway, for instance, surface
 20 reactions at the active site and electron drift-diffusion from the active site to the metal
 21 current collector.

22 We indicate the equilibrium quantities, such as electron and oxygen vacancy concentra-
 23 tion, with the superscript (0). In order to determine equilibrium concentrations of charge
 24 carriers, we consider the following gas phase and bulk defect reactions:



25 where the Kröger-Vink notation is used [14], i.e. $V_O^{\bullet\bullet}$ is a vacant site in the crystal, e' is an
 26 electron, and O_O^x an oxygen site in the crystal (superscripts \bullet , $'$ and x indicate respectively
 27 +1 charge, -1 charge and zero charge). At equilibrium the number of vacant sites per unit
 28 volume is $c_{ion}^{(0)}$, and the number of electrons per unit volume is $c_{e^{(0)}}$. At equilibrium the

1 following two quantities will be constants:

$$K_g = \frac{\tilde{p}_{H_2O}^2}{\tilde{p}_{H_2}^2 \tilde{p}_{O_2}} \quad (2a)$$

$$K_r = \left(\frac{c_{e\text{on}}^{(0)}}{B} \right)^2 \frac{c_{\text{ion}}^{(0)}}{B} \tilde{p}_{O_2}^{1/2} \quad (2b)$$

in addition to that, electroneutrality will be satisfied throught the sample:

$$1 + \frac{c_{e\text{on}}^{(0)}}{B} - 2 \frac{c_{\text{ion}}^{(0)}}{B} = 0 \quad (3)$$

2 where $\tilde{p}_k = \frac{p_k}{1\text{atm}}$ and p_k is the partial pressure of species k . In the dilute limit, at a given
 3 temperature and partial pressure, we solve for the equilibrium concentrations of vacancies
 4 $c_{\text{ion}}^{(0)} \approx B/2$ and electrons $c_{e\text{on}}^{(0)} \approx B \frac{\sqrt{2K_r}}{[Sm'_{Ce}]^{1.5} \tilde{p}_{O_2}^{0.25}}$.

5 Finally we assume that the mobilities u of all species are given in Tab. II, from [8].

6 III. BACKGROUND

7 A. Asymptotic Modeling of Mixed Conduction in the Bulk

8 A mixed conductor is a substance capable of conducting two or more charged species of
 9 opposite sign. Mass and charge transport in solids are described, at a mesoscopic level, by
 10 drift diffusion (DD) equations. The derivation of these equations is given in many textbooks,
 11 see for example [15]. For clarity we will shortly rewrite them here. For a mobile species m ,
 12 the continuity portion of the DD equations is expressed by equations of the form:

$$\frac{\partial c_m}{\partial t} + \nabla \cdot \mathbf{j}_m^P = \dot{\omega}_m \quad (4)$$

13 where c_m is the concentration of species m , \mathbf{j}_m^P is the particle (superscript P) flux of species
 14 m per unit area and $\dot{\omega}_m$ is its net rate of creation per unit volume.

15 We will assume the following phenomenological relationship for the flux of species m (this
 16 relation is valid for $\nabla T \simeq 0$ and $\nabla P \simeq 0$ [16]):

$$\mathbf{j}_m^P = -\frac{c_m D_m}{k_b T} \nabla \tilde{\mu}_m \quad (5)$$

where D_m and $\tilde{\mu}_m$ are respectively its diffusivity, are given by Einstein's relation $D_m = u_m k_b T / z_m$ (u_m is the mobility), and its electrochemical potential, which, in turn, is given by expression of the type:

$$\tilde{\mu}_m = \mu_m^0 + k_b T \log(c_m f_m(c_m, T, P)) + z_m e \phi \quad (6)$$

In the latter e is the elementary charge and ϕ is the electric potential, f_m is the activity of species m and z_m is its integer charge, i.e. -1 for electrons, +2 for oxygen vacancies in an oxide and μ_m^0 is a reference value. We also define the \star -electrochemical potential of a species m as:

$$\tilde{\mu}_m^* = \frac{\tilde{\mu}_m}{z_m} \quad (7)$$

1 The same equations are sometime expressed in a different way; if we define the conduc-
2 tivity $\sigma_m = \frac{e^2 c_m D_m z_m^2}{k_b T}$, we will deduce from Eqn.s 4 and 6 that:

$$\frac{\partial c_m}{\partial t} - \nabla \cdot \left\{ \left(D_m + \frac{\partial \log f_m}{\partial \log c_m} \right) \nabla c_m + \frac{\sigma_m}{z_m e} \nabla \phi \right\} = \dot{\omega}_m \quad (8)$$

3 Here we suppose the presence of two mobile species: oxygen vacancies, which we indicate
4 with the subscript *ion* ($z_{ion} = +2$), and electrons, subscript *eon* ($z_{eon} = -1$). The distri-
5 bution of electrons and vacancies is thus described by 3 equations: one for the electric field
6 (Poisson's equation for the potential) and two for the mobile species conservation. This set
7 of equations can be written as:

$$\Delta \phi = \frac{e}{\varepsilon} (B + c_{eon} - 2c_{ion}) \quad (9a)$$

$$\partial_t c_{eon} + \nabla \cdot \left(-D_{eon} c_{eon} \nabla \frac{\tilde{\mu}_{eon}}{k_B T} \right) = 0 \quad (9b)$$

$$\partial_t c_{ion} + \nabla \cdot \left(-D_{ion} c_{ion} \nabla \frac{\tilde{\mu}_{ion}}{k_B T} \right) = 0 \quad (9c)$$

8 where ε is the permittivity of the medium, B is the background dopant concentration in
9 number of particles per unit volume and where we have chosen $\dot{\omega}_{eon} = \dot{\omega}_{ion} = 0$. In the
10 dilute limit [12], [17], [18], [19] and [20], one has:

$$\tilde{\mu}_{eon} = k_B T \log \left(\frac{c_{eon}}{c_{eon}^0} \right) - e \phi + \tilde{\mu}_{eon}^0 \quad (10a)$$

$$\tilde{\mu}_{ion} = k_B T \log \left(\frac{c_{ion}}{c_{ion}^0} \right) + 2e \phi + \tilde{\mu}_{ion}^0 \quad (10b)$$

11 where c_{ion}^0 and c_{eon}^0 are reference values.

1 Non-dimensionalization of the Eqn.s 9 with respect to its relevant parameters proves
 2 to be crucial in order to understand appropriate time and length scales. We apply the
 3 transformations: $(\mathbf{x}, t) \rightarrow (\tilde{\mathbf{x}}, \tilde{t})$ such that $\mathbf{x} = l_c \tilde{\mathbf{x}}$ and $t = \tau \tilde{t}$. At this point we suppose the
 4 diffusivities D_{eon} and D_{ion} are uniform (we shall relax this approximation later). Also, we
 5 define $U_T = k_b T / e$, $\tilde{\phi} = \phi / U_T$, $\tau_n = l_c^2 / D_{eon}$, $\tau_p = l_c^2 / D_{ion}$ and $\tau = \min(\tau_n, \tau_p)$. Obviously
 6 $\nabla_x(\cdot) = \frac{1}{l_c} \nabla_{\tilde{x}}(\cdot)$ and $\partial_t(\cdot) = \frac{1}{\tau} \partial_{\tilde{t}}(\cdot)$. So Eqn. 9 becomes:

$$\Delta_{\tilde{x}} \tilde{\phi} = \frac{e l_c^2 B}{\varepsilon U_T} \left(1 + \frac{c_{eon}^{(0)}}{B} \frac{c_{eon}}{c_{eon}^{(0)}} - 2 \frac{c_{ion}^{(0)}}{B} \frac{c_{ion}}{c_{ion}^{(0)}} \right) \quad (11a)$$

$$\frac{\tau_n}{\tau} \partial_{\tilde{t}} \frac{c_{eon}}{c_{eon}^{(0)}} + \nabla_{\tilde{x}} \cdot \left(-\nabla_{\tilde{x}} \frac{c_{eon}}{c_{eon}^{(0)}} + \frac{c_{eon}}{c_{eon}^{(0)}} \nabla_{\tilde{x}} \tilde{\phi} \right) = 0 \quad (11b)$$

$$\frac{\tau_p}{\tau} \partial_{\tilde{t}} \frac{c_{ion}}{c_{ion}^{(0)}} - \nabla_{\tilde{x}} \cdot \left(\nabla_{\tilde{x}} \frac{c_{ion}}{c_{ion}^{(0)}} + 2 \frac{c_{ion}}{c_{ion}^{(0)}} \nabla_{\tilde{x}} \tilde{\phi} \right) = 0 \quad (11c)$$

where $c_{eon}^{(0)}$ and $c_{ion}^{(0)}$ are equilibrium values [9]. Define now the Debye length $\lambda_D = \sqrt{\frac{\varepsilon U_T}{eB}}$
 and $\lambda = \frac{l_c}{\lambda_D}$. We suppose $\lambda \gg 1$, which holds true for highly doped MIECs and sufficiently
 large characteristic dimensions, and we use singular perturbation of Eqn. 11a to obtain [21]:

$$1 + \frac{c_{eon}^{(0)}}{B} \frac{c_{eon}}{c_{eon}^{(0)}} - 2 \frac{c_{ion}^{(0)}}{B} \frac{c_{ion}}{c_{ion}^{(0)}} = 0 \quad (12)$$

7 In view of the latter, we can drop Eqn. 11a, thus we are left with Eqn.s 11b, 11c and 12. We
 8 now focus on impedance conditions, i.e. we suppose an off-equilibrium perturbation of the
 9 boundary conditions which in turn will slightly affect all unknowns (terms with superscript
 10 (1) are much smaller than the terms with superscript (0)):

$$\tilde{\phi} = \tilde{\phi}^{(1)} \quad (13a)$$

$$c_{eon} = c_{eon}^{(0)} + c_{eon}^{(1)} = c_{eon}^{(0)} \left(1 + \frac{c_{eon}^{(1)}}{c_{eon}^{(0)}} \right) \quad (13b)$$

$$c_{ion} = c_{ion}^{(0)} + c_{ion}^{(1)} = c_{ion}^{(0)} \left(1 + \frac{c_{ion}^{(1)}}{c_{ion}^{(0)}} \right) \quad (13c)$$

11

12 We set $n^{(1)} = \frac{c_{eon}^{(1)}}{c_{eon}^{(0)}}$ and $p^{(1)} = \frac{c_{ion}^{(1)}}{c_{ion}^{(0)}}$ and suppose $c_{eon}^{(0)}$, $c_{ion}^{(0)}$ are uniform and $\phi^{(0)} = 0$. If we
 13 also use the definitions of Eqn. 13 in the Eqns. 11b and 11c, we obtain:

$$\frac{\tau_n}{\tau} \partial_{\tilde{t}} (1 + n^{(1)}) + \nabla_{\tilde{x}} \cdot \left(-\nabla_{\tilde{x}} (1 + n^{(1)}) + (1 + n^{(1)}) \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) = 0 \quad (14a)$$

$$\frac{\tau_p}{\tau} \partial_{\tilde{t}} (1 + p^{(1)}) - \nabla_{\tilde{x}} \cdot \left(\nabla_{\tilde{x}} (1 + p^{(1)}) + 2(1 + p^{(1)}) \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) = 0 \quad (14b)$$

1

2 If we retain in Eqn. 14 only first order terms, we get:

$$\frac{\tau_n}{\tau} \partial_{\tilde{t}} n^{(1)} - \Delta_{\tilde{x}} n^{(1)} + \Delta_{\tilde{x}} \tilde{\phi}^{(1)} = 0 \quad (15a)$$

$$\frac{\tau_p}{\tau} \partial_{\tilde{t}} p^{(1)} - \Delta_{\tilde{x}} p^{(1)} - 2\Delta_{\tilde{x}} \tilde{\phi}^{(1)} = 0 \quad (15b)$$

3

4 The electroneutrality condition, Eqn. 12, at first order gives that $p^{(1)} = \frac{1}{2} \frac{c_{e0n}^{(0)}}{c_{ion}^{(0)}} n^{(1)} =$
 5 $\frac{1}{2} \frac{\bar{n}}{\bar{p}} n^{(1)}$. Thus defining:

$$\tau_n^* = \frac{\tau_n + \frac{\bar{n}}{4\bar{p}} \tau_p}{1 + \frac{\bar{n}}{4\bar{p}}} \quad (16a)$$

$$\tau_\phi^* = \frac{\tau_p - \tau_n}{1 + \frac{4\bar{p}}{\bar{n}}} \quad (16b)$$

6 helps rewrite the Eqn. 15 as:

$$\frac{\tau_n^*}{\tau} \partial_{\tilde{t}} n^{(1)} - \Delta_{\tilde{x}} n^{(1)} = 0 \quad (17a)$$

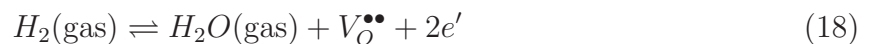
$$\frac{\tau_\phi^*}{\tau} \partial_{\tilde{t}} n^{(1)} - \Delta_{\tilde{x}} \tilde{\phi}^{(1)} = 0 \quad (17b)$$

7

8 **B. Boundary Conditions**

9 It follows from symmetry, Fig. 1, that $\partial_{\tilde{x}} \tilde{\phi}^{(1)} = \partial_{\tilde{x}} \tilde{n}^{(1)} = 0$ on Γ_2 and Γ_3 . Since the metal
 10 is ion-blocking, $\frac{1}{2} \frac{\bar{n}}{\bar{p}} \partial_{\tilde{y}} n^{(1)} + 2\partial_{\tilde{y}} \tilde{\phi}^{(1)} = 0$ will be satisfied on Γ_4 . We assume as well that the
 11 response of the metal to an electric perturbation is fast compared to the MIEC, from this
 12 it follows that we can take the electric potential $\tilde{\phi}^{(1)}$ uniform on Γ_4 . Thank to linearity and
 13 given the impedance setting, we can choose $\tilde{\phi}^{(1)} = \frac{1}{\sqrt{2\pi}} \Re \left(e^{i\omega\tau\tilde{t}} \right)$ on Γ_4 and $\tilde{\phi}^{(1)} = n^{(1)} = 0$
 14 on Γ_1 .

We assume the chemistry due to the reactions on Γ_5 has a finite speed and that it is correctly characterized by a one-step reaction, [22]. For simplicity we start from:



1 We also remark, [22], that the rates of injection of vacancies $\dot{\omega}_{ion,S}$ and electrons $\dot{\omega}_{eon,S}$
 2 at Γ_5 satisfy (subscript S indicates surface) the following two equations:

$$\begin{aligned}\dot{\omega}_{ion,S} &= \frac{1}{2}\dot{\omega}_{eon,S} \\ \dot{\omega}_{ion,S} &= k_f \tilde{p}_{H_2} - k_r \tilde{p}_{H_2} O c_{ion} c_{eon}^2\end{aligned}\quad (19)$$

3 where k_f is the forward rate of the reaction in Eqn. 18 and k_r is the reverse rate.

The latter gives, under small perturbation assumptions [22], a Chang-Jaffé boundary condition [23]:

$$-\dot{\omega}_{eon,S}^{(1)} = 4 \frac{D_{ion}}{l_c} \tilde{k}_f^0 \tilde{p}_{O_2}^{-1/4} \left(1 + \frac{c_{eon}^{(0)}}{4c_{ion}^{(0)}} \right) \tilde{p}_{H_2} n^{(1)} \quad (20)$$

4 We suppose $k_f = 2 \frac{D_{ion}}{l_c} \tilde{k}_f$ and $\tilde{k}_f = \tilde{k}_f^0 \tilde{p}_{O_2}^\beta \times \frac{\#particles}{m^3}$, [42] where we choose $\beta = 1/4$ [22].

5 Hence the y -flux of electrons and vacancies satisfies the following expression along
 6 Γ_5 : $\mathbf{j}_{eon}^P \cdot \mathbf{e}_y = 2\mathbf{j}_{ion}^P \cdot \mathbf{e}_y = -\dot{\omega}_{eon,S}$. If we define $\tilde{A}_\phi = \tilde{k}_f \frac{\tilde{p}_{H_2}}{c_{ion}^{(0)}} \left(1 - \frac{D_{ion}}{D_{eon}} \right)$ and $\tilde{A}_n =$
 7 $\tilde{k}_f \frac{\tilde{p}_{H_2}}{c_{ion}^{(0)}} \left(1 + 4 \frac{D_{ion} c_{ion}^{(0)}}{D_{eon} c_{eon}^{(0)}} \right)$, we can rewrite the boundary conditions on on Γ_5 as $\partial_{\tilde{y}} \tilde{\phi}^{(1)} = \tilde{A}_\phi n^{(1)}$
 8 and $\partial_{\tilde{y}} n^{(1)} = \tilde{A}_n n^{(1)}$.

9 C. Weak Formulation of the Model

10 If we Fourier transform Eqn.s 17 and the boundary conditions with respect to \tilde{t} [43], we
 11 find the following system of equations ($\hat{(\cdot)}$ indicates Fourier transformed quantity) [44] which
 12 we call IS equations:

$$i\omega \tau_n^* \hat{n}^{(1)} - \Delta \hat{n}^{(1)} = 0 \quad (21a)$$

$$i\omega \tau_\phi^* \hat{n}^{(1)} - \Delta \hat{\phi}^{(1)} = 0 \quad (21b)$$

with boundary conditions:

$$\left\{ \begin{array}{lll} \hat{\phi}^{(1)} = 0 & \wedge & \hat{n}^{(1)} = 0 & \text{on } \Gamma_1 \\ \partial_{\tilde{x}} \hat{\phi}^{(1)} = 0 & \wedge & \partial_{\tilde{x}} \hat{n}^{(1)} = 0 & \text{on } \Gamma_2 \quad \wedge \quad \Gamma_3 \\ \hat{\phi}^{(1)} = 1 & \wedge & \partial_{\tilde{y}} \hat{n}^{(1)} = -4 \frac{\tilde{p}}{\tilde{n}} \partial_{\tilde{y}} \hat{\phi}^{(1)} & \text{on } \Gamma_4 \\ \partial_{\tilde{y}} \hat{\phi}^{(1)} = \tilde{A}_\phi \hat{n}^{(1)} & \wedge & \partial_{\tilde{y}} \hat{n}^{(1)} = \tilde{A}_n \hat{n}^{(1)} & \text{on } \Gamma_5 \end{array} \right. \quad (22)$$

13 We can recast the Eqn. 21 and 22 in weak form taking as test functions $m_{Re}, m_{Im} \in$
 14 $H^1(\Omega \setminus \Gamma_1)$, $\psi_{Re}, \psi_{Im} \in H^1(\Omega \setminus (\Gamma_1 \cup \Gamma_4))$ [24]:

$$\begin{aligned} \omega\tau_n^* \int_{\Omega} \hat{n}_{Im}^{(1)} m_{Re} d\tilde{A} - \int_{\Omega} \nabla \hat{n}_{Re}^{(1)} \cdot \nabla m_{Re} d\tilde{A} + \int_{\Gamma_5} \tilde{A}_n \hat{n}_{Re}^{(1)} m_{Re} d\tilde{A} + \dots \\ - 4 \frac{\tilde{p}}{\tilde{n}} \int_{\Gamma_4} \partial_{\tilde{y}} \hat{\phi}_{Re}^{(1)} m_{Re} d\tilde{x} = 0 \end{aligned} \quad (23a)$$

$$\begin{aligned} \omega\tau_n^* \int_{\Omega} \hat{n}_{Re}^{(1)} m_{Im} d\tilde{A} + \int_{\Omega} \nabla \hat{n}_{Im}^{(1)} \cdot \nabla m_{Im} d\tilde{A} - \int_{\Gamma_5} \tilde{A}_n \hat{n}_{Im}^{(1)} m_{Im} d\tilde{x} \\ + 4 \frac{\tilde{p}}{\tilde{n}} \int_{\Gamma_4} \partial_{\tilde{y}} \hat{\phi}_{Im}^{(1)} m_{Im} d\tilde{x} = 0 \end{aligned} \quad (23b)$$

$$\omega\tau_{\phi}^* \int_{\Omega} \hat{n}_{Im}^{(1)} \psi_{Re} d\tilde{A} - \int_{\Omega} \nabla \hat{\phi}_{Re}^{(1)} \cdot \nabla \psi_{Re} d\tilde{A} + \int_{\Gamma_5} \tilde{A}_{\phi} \hat{n}_{Re}^{(1)} \psi_{Re} d\tilde{x} = 0 \quad (23c)$$

$$\omega\tau_{\phi}^* \int_{\Omega} \hat{n}_{Re}^{(1)} \psi_{Im} d\tilde{A} + \int_{\Omega} \nabla \hat{\phi}_{Im}^{(1)} \cdot \nabla \psi_{Im} d\tilde{A} - \int_{\Gamma_5} \tilde{A}_{\phi} \hat{n}_{Im}^{(1)} \psi_{Im} d\tilde{x} = 0 \quad (23d)$$

1

with the condition that:

$$\hat{\phi}_{Re}^{(1)} = 0 \quad \wedge \quad \hat{\phi}_{Im}^{(1)} = 0 \quad \text{on} \quad \Gamma_1 \quad (24a)$$

$$\hat{n}_{Re}^{(1)} = 0 \quad \wedge \quad \hat{n}_{Im}^{(1)} = 0 \quad \text{on} \quad \Gamma_1 \quad (24b)$$

$$\hat{\phi}_{Re}^{(1)} = 1 \quad \wedge \quad \hat{\phi}_{Im}^{(1)} = 0 \quad \text{on} \quad \Gamma_4 \quad (24c)$$

2

3 It is easy to show that the sum of the Eqn.s 23 is bounded and thus the bilinear form
4 associated to the weak formulation of Eqn.s 21 with 22 is continuous. Further, the problem
5 is weakly-coercive hence it admits one unique solution, [25].

6

D. Numerical Solution Procedure for the 2D Case

7 In order to solve numerically the Eqn.s 23 with boundary conditions Eqn.s 24 we em-
8 ploy an h-adapted finite element method (FEM), implemented with FreeFem++ [26]. The
9 governing equations are discretized on a triangular unstructured mesh using quadratic con-
10 tinuous basis functions with a centered third order bubble. We use a direct method to
11 solve the linear system following integration of Eqn.s 23 in the discretized mesh. Then the
12 mesh is adaptively refined at each solution step, up to nine refined solutions are found. The
13 a posteriori adaptation is performed the first six times against the 4 dimensional vector
14 $\left(\nabla \Re \left[\hat{\mu}_{e\omega}^{(1)} \right], \nabla \Re \left[\hat{\mu}_{i\omega}^{(1)} \right] \right)$ and subsequently against η_{ϵ} , see Appendix A. The h-adaptation

1 ensures high regularity of the H^1 a posteriori estimator [27], locally below 10^{-5} , and it guar-
 2 antees that the mesh is finer where sharper gradients occur. Independently of frequency,
 3 mesh adaptivity results in coarseness everywhere except in the vicinity of the interfaces, in
 4 particular the refinement increases towards the triple-phase boundary (the intersection of
 5 metal, oxide and gas phases, which is though to be a particularly active site for electrochem-
 6 ical reactions [11], [28]); this fact indicates strong non-linearities around that area. Finally
 7 we note that FreeFem++ execution time is comparable to custom-written C++ code and
 8 its speed is enhanced by the utilization of fast sparse linear solvers such as the multi-frontal
 9 package UMFPACK [29]. Due to the sparsity of the problem we make extensive use of this
 10 last feature.

11 We further note that the utilization of asymptotic expansion and Fourier transformation
 12 techniques, while guaranteeing linearity, has a great speed advantage over direct sinusoidal
 13 [30] and step relaxation techniques [31]. Further, this method can be directly used to
 14 examine chemical reactions within the cell and draw directly conclusions about fast and
 15 rate-limiting chemical reactions. Also, this procedure lends itself to direct error estimation
 16 and its implementation can be done automatically for a time-dependent problem [32].

17 E. 1D case: Analytical Solution

18 Since we also aim at comparing the 1D and 2D solutions, it is beneficial to revisit the 1D
 19 solution of Eqn.s 21, [6]. The solution $(\hat{n}^{(1)}, \hat{\phi}^{(1)})$ will satisfy (if $\omega \neq 0$):

$$\hat{n}^{(1)} = \sum_{\pm} a_{\pm} e^{\pm \sqrt{i} \sqrt{\tau_n^*} \omega \tilde{y}} \quad (25a)$$

$$\hat{\phi}^{(1)} = \hat{\phi}_0^{(1)} + (\hat{\phi}_0^{(1)})' \tilde{y} + \frac{\tau_{\phi}^*}{\tau_n^*} \hat{n}^{(1)} \quad (25b)$$

20

where for simplicity we indicate $\sqrt{i} = e^{i\frac{\pi}{4}}$. The boundary conditions, as in the 2D case,
 at $\tilde{y} = 0$ (Γ_1) are:

$$\hat{\phi}^{(1)} = 0 \quad \wedge \quad \hat{n}^{(1)} = 0 \quad (26)$$

1 The latter can help rewrite Eqn.s 25 as:

$$\hat{n}^{(1)} = 2a_+ \sinh \left(\sqrt{i} \sqrt{\tau_n^* \omega} \tilde{y} \right) \quad (27a)$$

$$\hat{\phi}^{(1)} = (\hat{\phi}_0^{(1)})' \tilde{y} + 2a_+ \frac{\tau_\phi^*}{\tau_n^*} \sinh \left(\sqrt{i} \sqrt{\tau_n^* \omega} \tilde{y} \right) \quad (27b)$$

2

3 If we set $\gamma_\phi = \frac{R_{ion}^\perp e l_c D_e c_{eon}^{(0)}}{U_T (1 + \frac{1}{4} \frac{\bar{n}}{p})}$ and $\gamma_n = \frac{1}{4} \frac{\bar{n}}{p} \gamma_\phi$, then at $\tilde{y} = l_2$ we have the following conditions,
4 [9]:

$$\hat{\phi}^{(1)} = 1 \quad \wedge \quad \hat{n}^{(1)} + \gamma_\phi \frac{d\hat{\phi}^{(1)}}{d\tilde{y}} + \gamma_n \frac{d\hat{n}^{(1)}}{d\tilde{y}} = 0 \quad (28)$$

5

6 The boundary conditions Eqn. 28 will lead to the determination of a_+ and $(\hat{\phi}_0^{(1)})'$ in Eqn. 27 and the 1D model leads to impedance of the form, [8], [33] and [34]:

$$Z_{1D}(\omega, \tilde{p}_{O_2}, T) = R_\infty + (R_0 - R_\infty) \left(1 + \frac{R_{ion} + R_{eon}}{2R_{ion}} \right) \frac{\tanh s}{s + \frac{R_{ion} + R_{eon}}{2R_{ion}^\perp} \tanh s} \quad (29)$$

7

where all the relevant terms are reported in Table III.

8 IV. RESULTS

9 A. Comparison to Experiments

10

11 The electron electrochemical potential drop across the sample, i.e. the electrochemical
12 potential difference between the top and bottom electrodes (Γ_4 and its symmetric reflection)
is given by the following expression:

$$\hat{V}^{(1)} = 2U_T \left[\langle (\hat{\mu}_e^{(1)})^\star \rangle_{\Gamma_4} - \langle (\hat{\mu}_e^{(1)})^\star \rangle_{\Gamma_1} \right] \quad (30)$$

where $\langle a \rangle_\Lambda$ indicates the average of the quantity a over the set Λ . At first order the \star -electrochemical potential is given by $(\hat{\mu}_e^{(1)})^\star = \hat{\phi}^{(1)} - \hat{n}^{(1)}$. The electric current density at the the two ends of the circuit is:

$$\hat{j}^{(1)} = \frac{D_{eon} e c_{eon}^{(0)} \int_{\Gamma_4} \nabla_{\tilde{x}} \frac{\hat{\mu}_{eon}^{(1)}}{k_b T} \cdot \mathbf{e}_y d\tilde{x}}{(W_1 + W_2) l_c} \quad (31)$$

Hence the 2D impedance is given by the expression:

$$Z_{2D}(\omega, \tilde{p}_{O_2}, T) = \hat{V}^{(1)} / \hat{j}^{(1)} \quad (32)$$

We define the error of the 2D impedance Z_{2D} with respect to experimental impedance Z_{1D} spectra Eqn. 29 as follows:

$$\varepsilon_F(\omega, \hat{p}_{O_2}, T) = \left| 1 - \frac{Z_{2D}(\omega, \tilde{p}_{O_2}, T)}{Z_{1D}(\omega, \tilde{p}_{O_2}, T)} \right| \quad (33)$$

1 For every data point, uniquely defined by the couple (\tilde{p}_{O_2}, T) , we fit the 2D data against
 2 the measured 1D equivalent circuit data in [9] by minimizing $\varepsilon_F(\omega, \tilde{p}_{O_2}, T)$ with respect to
 3 the surface reaction constant $\tilde{k}_f^0 = A\tilde{p}_{O_2}^\alpha$. We remark that \tilde{k}_f^0 is the sole parameter we allow
 4 to vary in this procedure and all other data is obtained from the literature and presented
 5 in Tab. IV. With only one parameter variation, we obtained excellent agreement between
 6 experimental results and 2D calculations, i.e. $\varepsilon_F(\omega, \hat{p}_{O_2}, T) < 2\%$. As an example, 2D results
 7 at four different oxygen partial pressures and at 650°C are shown in Fig. 3. We computed
 8 the \tilde{k}_f^0 by minimizing the ε_F for a total of 28 cases (7 pressures times 4 temperature). We
 9 report in Tab. IV the results of linear regression of these minimizing values (each line is
 10 derived on keeping the temperature fixed and varying \tilde{p}_{O_2}). We also write in Tab. IV, the
 11 95% confidence intervals for the fitting of A , i.e., $A \approx \bar{A} \pm \varepsilon_A$, and α , i.e., $\alpha = \bar{\alpha} \pm \varepsilon_\alpha$;
 12 we finally report the root mean square error σ and the adjusted R -squared, [35], regarding
 13 the latter, a value close to 1 indicates a perfect fit while negative values indicate poor data
 14 correlation. Directly from analysis of Tab. IV we deduce that \tilde{k}_f^0 fitting to a straight line is
 15 reasonable for "high" temperatures ($T \geq 550^\circ C$). We note that \tilde{k}_f^0 is temperature dependent
 16 via \bar{A} (\bar{A} decreases with T). Furthermore \tilde{k}_f^0 is slightly pressure dependent via the coefficient
 17 α , the average value of $\bar{\alpha} \approx 0.05 \geq 0$, however the error is of the same order of the slope.
 18 Hence the total rate of reaction is very likely to be $\dot{\omega}_{eom,S} \propto \tilde{p}_{O_2}^{-1/4+\beta}$ where β is somewhere
 19 in the set $[0, 0.1]$, most likely equal to 0.05.

20 B. The Polarization Resistance in Frequency Space

One of the goals of fuel cell science is to understand and possibly reduce the polarization resistance, i.e. that portion of the resistance due to electric field effects at interfaces. For that purpose it is key to identify and understand the main processes that intervene in

the definition of this quantity. Specifically, the area specific polarization resistance for our system is defined as [22]:

$$Z_{ion}^{\perp} = U_T \frac{\langle \hat{\mu}_{ion}^* \rangle_{\Gamma_5} - \langle \hat{\mu}_{eon}^* \rangle_{\Gamma_4}}{\hat{j}_{IP}^{(1)}} \quad (34)$$

1 where $\hat{j}_{IP}^{(1)} = \frac{1}{W_1+W_2} \int_{\Gamma_5} \dot{\omega}_{eon,S} dx$ is the ionic contribution to the area specific current.

The Z_{ion}^{\perp} can be understood as the sum of a surface Z_{surf} and a bulk polarization resistance, $Z_{bulk} = Z_{ion}^{\perp} - Z_{surf}$, where the Z_{surf} is the portion of the area-specific resistance due to effects of the exposed boundary Γ_5 and it is given by:

$$Z_{surf} = U_T \frac{\langle \hat{\mu}_{ion}^* \rangle_{\Gamma_5} - \langle \hat{\mu}_{eon}^* \rangle_{\Gamma_5}}{\hat{j}_{CP}^{(1)}} \quad (35)$$

2 In our model, by definition, the $Z_{surf} \in \mathbb{R}^+$ is proportional to $(1 + W_1/W_2)$ and inversely
3 proportional to both \tilde{p}_{H_2} and k_f :

$$Z_{surf} = \frac{1}{2} \left(1 + \frac{W_1}{W_2} \right) \frac{U_T}{ek_f \tilde{p}_{H_2}} \quad (36)$$

4 The fraction $f_{surf} = \frac{Z_{surf}}{Z_{ion}^{\perp}}$ indicates than what portion of the polarization impedance is
5 due to surface effects. From Fig. 4 we note two fundamental facts: first, as we expect, at
6 "lower" injection rates the f_{surf} increases, physically this means that that if the chemistry
7 is sufficiently slow it will dominate the polarization resistance leading to an f_{surf} of approx-
8 imately unity. Second, we notice frequency dependent behavior of R_{ion}^{\perp} . Our computations
9 show that f_{surf} decreases with ω , while the dephasing between Z_{surf} and Z_{ion}^{\perp} , described by
10 $\arg(f_{surf})$, increases with \tilde{k}_f^0 and decreases with ω . The behavior of f_{surf} in phase space
11 clearly shows that Z_{surf} includes two interrelated processes:

- 12 1. reactions on the surface exposed to the gas;
- 13 2. transport of charged species in MIEC.

14 Within this framework, as ω increases, the losses in the polarization due to drift diffusion
15 increase and surpass the (constant) reaction or surface losses.

1 C. Analysis of the 2D Solution

2 1. Qualitative Considerations

3 We can then use the framework to study the two complex electrochemical potentials
4 $\hat{\mu}_{\text{eon}} = \hat{n}^{(1)} - \hat{\phi}^{(1)}$ and $\hat{\mu}_{\text{ion}} = \hat{\phi}^{(1)} + \frac{\bar{n}}{2p}\hat{n}^{(1)}$ as functions of frequency. In Figs. 5 and 6 we plot
5 the 2D distributions of the latter in the computational domain at $T = 650^\circ\text{C}$, $\tilde{p}_{\text{O}_2} = 10^{-25}$
6 and $\tilde{k}_f^0 = 10^{32}$ with frequency ω increasing from 10^{-3} to 10^5 rad/s . Thank to the Figs. 5 and
7 6, we can address the qualitative behavior of the solution. We first analyze the qualitative
8 distribution of fluxes: from the gradient of $|\hat{\mu}_{\text{eon}}|$, which gives an idea of electron flux, that
9 electrons flow from the gas|ceria interface Γ_5 onto the ceria|metal interface Γ_4 through a
10 cross-plane current \hat{I}_g^{CP} , and concurrently electrons flow onto the ceria|metal interface Γ_5
11 from its mirror symmetric counterpart. Similarly the MIEC|metal interface is blocking to
12 vacancies, hereby the vacancies correctly flow from the bottom to the top ceria|gas interface
13 Γ_5 . It is also clear that the complex potential of the electrons $\hat{\mu}_{\text{eon}}$ changes significantly as
14 ω increases, while $\hat{\mu}_{\text{ion}}$ is relatively unaffected. The penetration depth, which is defined as
15 the distance from Γ_4 where surface electrons can penetrate into the bulk, decreases with ω
16 as the 1D model hints (in Eqn.s 27 the solution decays exponentially with $1/\sqrt{\tau_n^*\omega}$). As ω
17 increases, the dephasing of $\hat{\mu}_{\text{eon}}$ first increases and then decreases and it is weakly dependent
18 upon the distance from Γ_4 , or conversely, the penetration depth into the MIEC. We notice
19 that the same dephasing increases then decreases for $\hat{\mu}_{\text{ion}}$. However, while for the vacancies,
20 the behavior of $|\hat{\mu}_{\text{ion}}|$ and $\arg(\hat{\mu}_{\text{ion}})$ is qualitatively the same, this is not the case for the
21 electrons, where through a wide array of ω 's, the qualitative behavior of $|\hat{\mu}_{\text{eon}}|$ and $\arg(\hat{\mu}_{\text{eon}})$
22 is distinctly different.

Deriving the electronic and ionic currents from the computations requires some care and
it will not simply be $\nabla|\hat{\mu}_m|$. For example, for electrons, we note that:

$$\tilde{\mu}_{\text{eon}}^{(1)} = (n^{(1)} - \phi^{(1)}) e^{i\omega t} \quad (37)$$

We will call the complex current $\mathbf{j}_{\text{eon}}^{\text{C}}$:

$$\mathbf{j}_{\text{eon}}^{\text{C}} = c_{\text{eon}}^{(0)} D_{\text{eon}} \mathcal{F}^{-1}[\nabla \hat{\mu}_{\text{eon}}^{(1)}] \quad (38)$$

23 the physical current will be [45]:

$$\mathbf{j}_{\text{eon}} = \Re(\mathbf{j}_{\text{eon}}^{\text{C}}) \quad (39)$$

1 In order to compare the 1D and 2D solutions qualitatively, we first focus on the case $\omega = 0$
 2 where $k_f^{(0)} = 10^{32}$, and we shrink the size of the slab while keeping the same framework and
 3 model parameters. This corresponds to a decrease of the aspect ratio of the sample defined
 4 as $AR = \frac{l_2}{W_1+W_2}$. We show in Fig. 8 the results of the computations in the case where the
 5 conditions are very reducing. We depict what happens to R_{ion} , R_{eon} , R_{ion}^\perp and f_{surf} as AR
 6 changes. We notice that decreasing AR corresponds to an increase in effective electronic
 7 and ionic resistance compared to the ideal case computed according to Tab. III which in
 8 turn corresponds to $AR \rightarrow \infty$. Deviations from ideality occur already for $AR \approx 25$, hence
 9 even for reasonably large AR the ionic and electronic resistances deviate from the ideal 1D
 10 case, this is clearly shown in Figs 8 a and b. The same applies to the polarization resistance
 11 R_{ion}^\perp , Fig. 8c, which is flat above $AR \approx 25$, below this value R_{ion}^\perp sharply increases due to
 12 bulk polarization effects. As the deviation from the 1D setting starts, not only ionic and
 13 electronic resistivity change, but so does the relative importance of surface and drift diffusion
 14 effects. Hence the polarization resistance is thickness-dependent, and the dependence is due
 15 to the emergence of two-dimensional effects. The increase in drift diffusion resistance due
 16 to the motion of electrons from Γ_5 to Γ_4 is also shown in the f_{surf} which increases with the
 17 AR reaching unity for $AR \rightarrow \infty$. This effect is even clearer if we plot the electrochemical
 18 potentials of electrons and vacancies at $\omega = 0$, we note a shrinking of the affected area as
 19 the sample thickness decreases corresponding to an increase of polarization resistance. This
 20 effect is purely 2D and cannot be studied using a 1D model.

21 2. Quantitative Analysis

22 In order to compare the 1D and 2D solution quantitatively we define the following two
 23 functionals:

$$\nu [\mu_{1D}, \mu_{2D}, \tilde{y}, \omega] = \frac{1}{W_1 + W_2} \frac{\int_{y'=\tilde{y}} |\mu_{1D}(y', \omega) - \mu_{2D}(\tilde{x}, y', \omega)| d\tilde{x}}{|\mu_{1D}(l_2, \omega)|} \quad (40a)$$

$$\zeta [\mu_{1D}, \mu_{2D}, \tilde{y}, \omega] = \frac{1}{W_1 + W_2} \frac{\left| \int_{y'=\tilde{y}} (\mu_{1D}(y', \omega) - \mu_{2D}(\tilde{x}, y', \omega)) d\tilde{x} \right|}{|\mu_{1D}(l_2, \omega)|} \quad (40b)$$

1 The functional ν describes the "pointwise" distance between 1D and 2D solutions of $\hat{\mu}$
 2 at a section \tilde{y} and the functional ζ describes the "average" distance between 1D and 2D
 3 descriptions. Physically ν indicates how far 1D and 2D electrochemical potential are, while
 4 ζ "measures" the soundness of fitting a 1D case with the 2D model. We can examine the
 5 applicability of the 1D approximation for data fitting via ζ .

6 In order to further compare the 2D model and 1D model and demonstrate the importance
 7 of 2D effects adjacent to the injection sites, the "pointwise" distance ν and the "average"
 8 distance ζ defined by Eqn.s 40b are computed at the same conditions $(T, \tilde{p}_{O_2}, \tilde{k}_f^0)$ in the
 9 frequency range of $10^{-3} \leq \omega \leq 10^5$ rad/s along the symmetry axis Γ_2 , Fig. 9. In the
 10 first line we plot the case where the sample is very thick with respect to the horizontal
 11 dimension ($AR = 125$), both the $\nu_{eon}(\tilde{y}, \omega) = \nu[\mu_{eon,1D}, \mu_{eon,2D}, \tilde{y}]$ and the $\zeta_{ion}(\tilde{y}, \omega) =$
 12 $\zeta[\mu_{ion,1D}, \mu_{ion,2D}, \tilde{y}]$ are extremely small and the adjacency between 1D and 2D impedance
 13 is near perfect. If we decrease AR to 12.5, then the 1D and 2D solutions tend to be further
 14 apart with $\nu_e \approx 25\%$ and ζ_e up to 20%. The difference between the two further increases at
 15 $AR = 5$ where the difference between impedance spectra is significant.

16 V. THE EFFECT OF DIFFUSIVITY GRADIENTS

17 A. Extension of the Model

18 Interface effects are one of the biggest sources of uncertainty in doped ionics because
 19 impurities in doped materials tend to segregate near interfaces and affect electro-catalytic
 20 processes, absorption and diffusivities near the affected interfaces. Many studies, for exam-
 21 ple [36], [37] and [38], have attempted to address these issues. However, to the authors'
 22 knowledge, no continuum model has addressed yet the relationship of these changes to po-
 23 larization resistance nor to impedance spectra. In this part of the paper we intend to address
 24 the effects of non uniform diffusivities, which are localized near the interfaces, and which
 25 we imagine are due to impurity segregation at the exposed surface (Γ_5 in Fig. 1) and to the
 26 MIEC|metal interface (Γ_4)

We shall assume that diffusivities near the MIEC|Gas interface and MIEC|Metal inter-
 faces have non-zero derivatives only along the y direction. We further assume that diffusive
 effects are symmetric on both ends of the sample $y = \pm l_2$, hence do not affect our initial

symmetry assumptions. Lastly we suppose that the functional form of the diffusivities are known in the MIEC and are given by:

$$D_m^* = 1 + \left(\frac{D_m^{SURF}}{D_m^{BULK}} - 1 \right) e^{-\frac{|l_c \tilde{y} \pm l_2|}{\lambda_m}} \quad (41)$$

1 where m can be either *eon* or *ion*, and λ_m , the length scale of diffusive changes, is much
 2 smaller than l_c , the characteristic length-scale of the sample ($\lambda_m \ll l_c$). We stress again
 3 that the main assumptions are that the diffusivity gradients parallel to the interfaces are
 4 null and that the diffusivity gradients do not affect bulk properties of the material nor the
 5 defect chemistry. In other words, near-interface effects involve only diffusivities.

6 Under the same small perturbation assumptions we used above we can deduce that the
 7 equations that describe the impedance spectra behavior of ions and electrons are given
 8 by [46]:

$$n^{(1)} = \frac{\bar{n}}{\bar{p}} p^{(1)} \quad (42a)$$

$$\frac{\tau_n}{\tau} \partial_{\tilde{x}} n^{(1)} + \nabla_{\tilde{x}} \cdot \left(-D_{eon}^* \left(\nabla_{\tilde{x}} n^{(1)} - \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) \right) = 0 \quad (42b)$$

$$\frac{\tau_p}{\tau} \partial_{\tilde{x}} p^{(1)} + \nabla_{\tilde{x}} \cdot \left(-D_{ion}^* \left(\nabla_{\tilde{x}} p^{(1)} + 2 \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) \right) = 0 \quad (42c)$$

9 The sum of the Eqns. 42 and their weighted difference lead to (see appendix B):

$$\frac{\tau_n^*}{\tau} \partial_{\tilde{x}} n^{(1)} + \nabla_{\tilde{x}} \cdot \left(-a_{11} \nabla_{\tilde{x}} n^{(1)} - a_{12} \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) = 0 \quad (43a)$$

$$\frac{\tau_\phi^*}{\tau} \partial_{\tilde{x}} n^{(1)} + \nabla_{\tilde{x}} \cdot \left(-a_{21} \nabla_{\tilde{x}} n^{(1)} - a_{22} \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) = 0 \quad (43b)$$

10 where:

$$a_{11} = \frac{D_{eon}^* + \frac{\bar{n}}{4\bar{p}} D_{ion}^*}{1 + \frac{\bar{n}}{4\bar{p}}} ; a_{12} = \frac{D_{ion}^* - D_{eon}^*}{1 + \frac{\bar{n}}{4\bar{p}}} \quad (44a)$$

$$a_{21} = \frac{D_{ion}^* - D_{eon}^*}{1 + \frac{4\bar{p}}{\bar{n}}} ; a_{22} = \frac{D_{eon}^* + \frac{4\bar{p}}{\bar{n}} D_{ion}^*}{1 + \frac{4\bar{p}}{\bar{n}}} \quad (44b)$$

11

12 The Eqn.s 43 with appropriate boundary conditions, Eqn.s 22, are quasi-linear and hence
 13 can be Fourier transformed. In short they can be recast in weak form as in Eqns. 23:

$$\begin{aligned} \omega\tau_n^* \int_{\Omega} \hat{n}_{Im}^{(1)} m_{Re} d\tilde{A} &- \int_{\Omega} a_{11} \nabla \hat{n}_{Re}^{(1)} \cdot \nabla m_{Re} d\tilde{A} - \int_{\Omega} a_{12} \nabla \hat{\phi}_{Re}^{(1)} \cdot \nabla m_{Re} d\tilde{A} + \dots \\ &\dots + \int_{\Gamma_5} \tilde{A}_{n,2} \hat{n}_{Re}^{(1)} m_{Re} d\tilde{A} - 4 \frac{\tilde{p}}{\tilde{n}} \int_{\Gamma_4} \partial_{\tilde{y}} \hat{\phi}_{Re}^{(1)} m_{Re} d\tilde{x} = 0 \end{aligned} \quad (45a)$$

$$\begin{aligned} \omega\tau_n^* \int_{\Omega} \hat{n}_{Re}^{(1)} m_{Im} d\tilde{A} &+ \int_{\Omega} a_{11} \nabla \hat{n}_{Im}^{(1)} \cdot \nabla m_{Im} d\tilde{A} + \int_{\Omega} a_{12} \nabla \hat{\phi}_{Im}^{(1)} \cdot \nabla m_{Im} d\tilde{A} - \dots \\ &\dots - \int_{\Gamma_5} \tilde{A}_{n,2} \hat{n}_{Im}^{(1)} m_{Im} d\tilde{x} + 4 \frac{\tilde{p}}{\tilde{n}} \int_{\Gamma_4} \partial_{\tilde{y}} \hat{\phi}_{Im}^{(1)} m_{Im} d\tilde{x} = 0 \end{aligned} \quad (45b)$$

$$\begin{aligned} \omega\tau_{\phi}^* \int_{\Omega} \hat{n}_{Im}^{(1)} \psi_{Re} d\tilde{A} &- \int_{\Omega} a_{21} \nabla \hat{n}_{Re}^{(1)} \cdot \nabla \psi_{Re} d\tilde{A} - \int_{\Omega} a_{22} \nabla \hat{\phi}_{Re}^{(1)} \cdot \nabla \psi_{Re} d\tilde{A} \\ &+ \int_{\Gamma_5} \tilde{A}_{\phi,2} \hat{n}_{Re}^{(1)} \psi_{Re} d\tilde{x} = 0 \end{aligned} \quad (45c)$$

$$\begin{aligned} \omega\tau_{\phi}^* \int_{\Omega} \hat{n}_{Re}^{(1)} \psi_{Im} d\tilde{A} &+ \int_{\Omega} a_{21} \nabla \hat{n}_{Im}^{(1)} \cdot \nabla \psi_{Im} d\tilde{A} + \int_{\Omega} a_{22} \nabla \hat{\phi}_{Im}^{(1)} \cdot \nabla \psi_{Im} d\tilde{A} \\ &- \int_{\Gamma_5} \tilde{A}_{\phi,2} \hat{n}_{Im}^{(1)} \psi_{Im} d\tilde{x} = 0 \end{aligned} \quad (45d)$$

1

2 where:

$$\tilde{A}_{n,2} = a_{11} \tilde{A}_n + a_{12} \tilde{A}_{\phi} \quad (46)$$

$$\tilde{A}_{\phi,2} = a_{21} \tilde{A}_n + a_{12} \tilde{A}_{\phi} \quad (47)$$

$$(48)$$

3 If we change the diffusivity of vacancies at the gas|ceria (Γ_5) and metal|ceria (Γ_4) interface
 4 by changing α_{ion} , we need to adjust the \tilde{k}_f^0 in order to keep the same rate of injection $\dot{\omega}_{con}^S$,
 5 Eqn. 20. We will proceed as follows:

$$\tilde{k}_f^{(0)}(\alpha_{ion}) = \frac{(\alpha_{ion})_{ref}}{\alpha_{ion}} \left(\tilde{k}_f^0 \right)_{ref} \quad (49)$$

6 Numerically we use the same approach described for the linear case but we need the
 7 error estimator to account for off-diagonal and space dependent parameters, Eqn.s 44 (in
 8 the linear case $a_{11} = a_{22} = 1$, $a_{12} = a_{21} = 0$).

9 Finally we note that we assume that the model holds for length-scales just one order
 10 of magnitude greater than the lattice parameter [39]. This approximation can be justified
 11 heuristically using the work of [40] and [41], which shows that deviations of the continuum
 12 drift-diffusion approach from atomistic models are usually small, even in cases where field
 13 effects are big.

B. Results of the Model

We first ran the model at steady state ($\omega = 0$) with the objective to analyze the $f_{surf} = \frac{R_{surf}}{R_{ion}}$ at $\omega = 0$ for a wide array of parameters $\alpha_{eon} = D_{eon}^{SURF}/D_{eon}^{BULK}$ and $\alpha_{ion} = D_{ion}^{SURF}/D_{ion}^{BULK}$, where $\alpha_{eon} = \alpha_{ion}$ and $\lambda_{eon} = \lambda_{ion}$ at varying $\tilde{k}_f^{(0)}$. For reasonable fitted values (Tab. IV) and for a wide parameter set, we show that the polarization resistance is surface dominated making $f_{surf} \approx 1$ robustly.

If chemical reaction rates are "sufficiently" slow (e.g. $\tilde{k}_f^0 \approx 10^{32}$) and if the sample is sufficiently thick, then the polarization resistance is dominated by surface effects in the linear case ($\alpha_{ion} = 1$), corresponding to an absence of diffusive gradients at the exposed surface. If impurities are present at the exposed surface, diffusivities of charged species may change and hence one could argue that the polarization resistance is not surface-dominated. In order to address this point, we ran two limiting cases, one featuring "slow" chemistry ($\tilde{k}_f^0(\alpha_{ion} = 1) \approx 10^{32}$) and the other one at "fast" chemistry ($\tilde{k}_f^0(\alpha_{ion} = 1) \approx 10^{34}$). We present the results of these calculations in Fig. 10 where we plot f_{surf} as a function of both $\alpha_{ion} = \alpha_{eon}$ and the diffusive gradients $\lambda_{ion} = \lambda_{eon}$. We notice from Fig. 10a that f_{surf} is very close to unity for two order of variation of surface-to-bulk diffusivity ratio $0.1 \leq \alpha_{ion} \leq 10$ and for a wide span of diffusivity length-scales $5nm \leq \lambda_{ion} \leq 1\mu m$. This indicates that if we perturb the the surface diffusivity up to one orders of magnitude with respect to its bulk value its impact on polarization resistance is minimal. The qualitative effect on the impedance is also small as shown for a variety of cases in Fig. 11.

If we choose a "fast" chemistry condition instead, e.g. $\tilde{k}_f^0 \approx 10^{34}$, the situation changes significantly from the base case ($\alpha_{ion} = 1$), Fig. 11b. In this Figure we focus on points A through D. (Pt. A), having $\alpha_{ion} = 0.1$ and $\lambda_{ion} = 5nm$, indicates that near surface diffusivities are an order of magnitude lower than their bulk value and this deviation is concentrated near the surface: in this case the polarization resistance is drift-diffusion dominated. If the diffusive length scale is increased to $\lambda_{ion} = 1\mu m$, while keeping $\alpha_{ion} = 0.1$, (Pt. B), the f_{surf} will not decrease much further. Starting from (Pt.A) we can move to (Pt.C), where diffusivity gradients are sharp ($\lambda_{ion} = 5nm$) but the diffusivities at the surface are an order of magnitude greater than its bulk value. In this case, the f_{surf} increases because of the increase in the bulk diffusivity. Going to (Pt. C) to (Pt. D) increases the length-scale of the diffusive effects leading in turn to bigger increase of f_{surf} .

1 We can summarize our findings as follows:

- 2 1. if the rate of injection of electrons is sufficiently "small" (slow chemistry) and of the
3 order of the fitted values reported in Tab. IV, then the diffusivity gradients localized
4 at interfaces will affect little the polarization resistance and the impedance spectra;
- 5 2. if the chemistry is sufficiently fast, sharp changes in diffusivity can affect strongly not
6 only the impedance behavior but also the polatization, in particular if the diffusivi-
7 ties increase sufficiently strictly near the interfaces, the polarization effects will shift
8 to be surface dominated, while a decrease is associated to drift-diffusion dominated
9 polarization resistance.

10 VI. CONCLUDING REMARKS

11 A general two-dimensional numerical framework has been developed for the coupled sur-
12 face chemistry, electrochemistry and transport processes in mixed conductors based on the
13 finite element method. As a specialized application of the framework, a time-dependent
14 model was formulated based on first-principles for the AC impedance spectra (IS) of a
15 samaria doped ceria (SDC) electrolyte with symmetric metal patterns on both sides, and
16 the IS was simulated for typical fuel cell operation conditions in a uniform gas atmosphere
17 (H_2 , H_2O , Ar) at thermodynamic equilibrium using the small perturbation technique.

18 The validity of the model is demonstrated by fitting to experimental (1D) impedance
19 spectra data of an SDC cell in literature, varying only the reaction rate at the SDC-gas in-
20 terface. Excellent agreement ($\leq 2\%$ error) was obtained. We then numerically investigated
21 the influence of the variation of several parameters on the polarization resistance and the
22 impedance spectra, especially within regimes not probable for the 1D studies. Our calcula-
23 tion shows that the 2D effect of cell thickness variation on the spectra becomes pronounced
24 as the aspect ratio goes below a certain threshold (25 for this work); surface reaction domi-
25 nates the polarization resistance when the injection rate at the SDC surface exposed to gas
26 is sufficiently slow; sharp gradients in diffusion coefficient strongly influence both impedance
27 behavior and polarization when surface chemistry is sufficiently fast.

28 The discussions in this work provide useful insights into the correlation between materials
29 properties of SDC and its applications in fuel cells, intensely studied by the solid oxide fuel

1 cell researchers. In addition, the geometric capability (up to 3D) and high computation
2 efficiency makes this numerical framework an ideal tool for the general study of mixed
3 conductors.

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APPENDIX A: ERROR ESTIMATOR AND REFINEMENT STRATEGY

The local residual for n_{Re} , at a triangular element K of the mesh, can be computed as follows [27]:

$$\begin{aligned} \eta_{k, n_{Re}} = & \int_K \left| \nabla \cdot \left(a_{11} \nabla \hat{n}_{Re,h}^{(1)} + a_{12} \nabla \hat{\phi}_{Re,h}^{(1)} \right) - \omega \tau_n^* \hat{n}_{Im,h}^{(1)} \right| h^2 + \left[\left[a_{11} \frac{\partial \hat{n}_{Re,h}^{(1)}}{\partial \mathbf{n}} + a_{12} \frac{\partial \hat{\phi}_{Re,h}^{(1)}}{\partial \mathbf{n}} \right] \right] h_K^{1/2} \\ & + \int_{\Gamma_5 \cap K} \left| \tilde{A}_{n,2} \hat{n}_{Re,h}^{(1)} - \partial_{\tilde{y}} \hat{n}_{Re,h}^{(1)} \right| h^2 + \int_{\Gamma_4 \cap K} \left| \partial_{\tilde{y}} \hat{n}_{Re}^{(1)} - 4 \frac{\bar{p}}{\bar{n}} \partial_{\tilde{y}} \hat{n}_{Re,h}^{(1)} \right| h^2 + \int_{(\Gamma_2 \cup \Gamma_3) \cap K} \left| \partial_{\tilde{x}} \hat{n}_{Re}^{(1)} \right| h^2 \end{aligned} \quad (\text{A1})$$

where $\llbracket a \rrbracket$ is the jump of the quantity a across the faces of K , h is a measure of the size K , while h_K is the measure of the size of the sides of K . Similar residuals can be found for $n_{Im}^{(1)}$, $\phi_{Re}^{(1)}$, $\phi_{Im}^{(1)}$. Their sum $\sum_k r_k$ constitutes a reasonable local a posteriori error estimator. $\sum_k r_k$ is a weakly coercive upper bound for $a \|u\|_{L_2} - b \|\nabla u\|_{L_2}$ where a and b are constants and $u = (n_{Re}^{(1)}, n_{Im}^{(1)}, \phi_{Re}^{(1)}, \phi_{Im}^{(1)})$

APPENDIX B: DERIVATION OF THE NON-LINEAR IMPEDANCE SPECTRA EQUATIONS

We start with the electro-neutral form of the drift-diffusion equations, where we assume that the diffusion coefficients normalized with respect to their bulk value $D_m^* = D_m^{\text{SURF}} / D_m^{\text{BULK}}$:

$$\frac{\tau_n}{\tau} \partial_{\tilde{t}} n^{(1)} + \nabla_{\tilde{x}} \cdot \left(-D_{eon}^* \left(\nabla_{\tilde{x}} n^{(1)} - \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) \right) = 0 \quad (\text{B1a})$$

$$\frac{\bar{n}}{4\bar{p}} \frac{\tau_p}{\tau} \partial_{\tilde{t}} n^{(1)} + \nabla_{\tilde{x}} \cdot \left(-D_{ion}^* \left(\frac{\bar{n}}{4\bar{p}} \nabla_{\tilde{x}} n^{(1)} + \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) \right) = 0 \quad (\text{B1b})$$

We first sum the Eqn.s B1a and B1b and obtain:

$$\left(\frac{\tau_n}{\tau} + \frac{\bar{n}}{4\bar{p}} \frac{\tau_p}{\tau} \right) \partial_{\tilde{t}} n^{(1)} + \nabla_{\tilde{x}} \cdot \left(- \left(D_{eon}^* + \frac{\bar{n}}{4\bar{p}} D_{ion}^* \right) \nabla_{\tilde{x}} n^{(1)} - (D_{ion}^* - D_{eon}^*) \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) = 0 \quad (\text{B2})$$

Finally we multiply Eqn. B1b by $\frac{4\bar{p}}{\bar{n}}$ and sum to Eqn B1a:

$$\left(\frac{\tau_p}{\tau} - \frac{\tau_n}{\tau} \right) \partial_{\tilde{t}} n^{(1)} + \nabla_{\tilde{x}} \cdot \left(- (D_{ion}^* - D_{eon}^*) \nabla_{\tilde{x}} n^{(1)} - \left(D_{eon}^* + \frac{4\bar{p}}{\bar{n}} D_{ion}^* \right) \nabla_{\tilde{x}} \tilde{\phi}^{(1)} \right) = 0 \quad (\text{B3})$$

¹ From the and , the Eqn.s 43 follow immediately and so do their coefficients given in
² Eqn.s 44 .

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- 4 $\tilde{k}_f^0 \approx 10^{32}$, so $k_f \approx 10^{32} \times \frac{10^{-10}}{10^{-5}} \times 10^{-6} = 10^{21} \frac{\#particles}{m^2} \approx 10^{-3} \frac{mol}{m^2} \approx 10^{-7} \frac{mol}{cm^2}$
- 5 [43] We choose unitary Fourier transform $\hat{f}(\omega) = \frac{1}{\sqrt{2\pi}} \int_{-\infty}^{\infty} f(x)e^{-i\omega x} dx$
- 6 [44] We factored out the Dirac distribution that comes out of Fourier transformation of an expo-
- 7 nential
- 8 [45] We remark that for complex valued function μ in general we have $abs(\nabla\tilde{\mu}) \neq \nabla(abs(\mu))$
- 9 [46] In order to ensure linearity, we assume that $\left|D_k n^{(1)} \nabla \tilde{\phi}^{(1)}\right| \ll \left|D_k \nabla n^{(1)}\right| \approx \left|D_k \nabla \tilde{\phi}\right|$

TABLE I: Data for the domain geometry and background doping

$W_1 = 1.5 \mu m$
$W_2 = 2.5 \mu m$
$l_2 = 500 \mu m$
$l_c = 10 \mu m$
$B = 3.47 \times 10^{+27} \frac{\#particles}{m^3}$

TABLE II: Temperature range and material constants for the simulations.

T	$500^\circ C$	$550^\circ C$	$600^\circ C$	$650^\circ C$
K_g	5.059E+27	4.814E+25	7.757E+23	1.944E+22
K_r	5.008E-22	2.263E-20	6.610E-19	1.340E-17
$u_{eon} \left[\frac{m^2}{V^2 s} \right]$	4.762E-8	6.257E-8	6.873E-8	8.123E-8
$u_{ion} \left[\frac{m^2}{V^2 s} \right]$	1.166E-9	2.070E-9	3.359E-9	4.936E-9

TABLE III: Definitions of the terms in the 1D model

R_{ion}^\perp	Measured
R_{eon}	$2l_2/\sigma_{eon}$
R_{ion}	$2l_2/\sigma_{ion}$
R_0	$1/(1/R_{eon} + 1/(R_{ion} + 2R_{ion}^\perp))$
R_∞	$1/(1/R_{eon} + 1/R_{ion})$
C_{chem}	$\frac{e^2}{k_b T} 2l_2 / \left(1/(z_{eon}^2 c_{eon}^{(0)}) + 1/(z_{ion}^2 c_{ion}^{(0)}) \right)$
\tilde{D}	$4l_2^2 / ((R_{ion} + R_{eon}) C_{chem})$
s	$\sqrt{i4\omega l_2^2 / (4\tilde{D})}$

TABLE IV: Fitted values of $\tilde{k}_f^0 = A\tilde{p}_{O_2}^\alpha$, 95% confidence interval

T [$^{\circ}C$]	$\log_{10} \bar{A}$	$\log_{10} \varepsilon_A$	$\bar{\alpha}$	ε_α	R^2	σ
500	32.48	0.150	0.05349	0.1655	-0.0439	0.1577
550	32.10	0.045	0.04160	0.0482	0.7622	0.04589
600	32.02	0.055	0.06674	0.0637	0.5378	0.06067
650	31.95	0.055	0.05596	0.0623	0.4981	0.05938

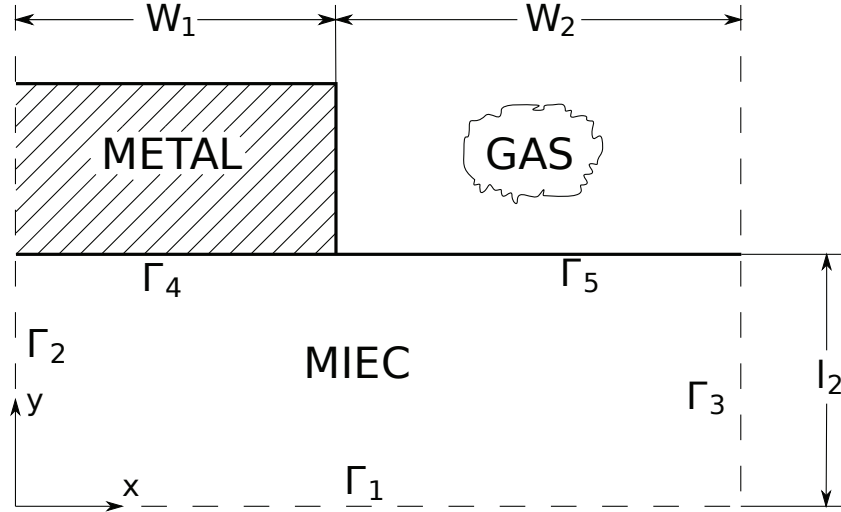


FIG. 1: Schematic depiction of the domain under study with annotation of the boundary names and dimensions. The domain is composed by an MIEC slab of half-thickness l_2 which is mirror symmetric with respect to Γ_1 . On top of the slab there is a metal stripe infinitely long deposited over the surface Γ_4 , the surface Γ_5 is exposed to the gas phase. The overall sample is mirror symmetric with respect to Γ_2 and Γ_3 .

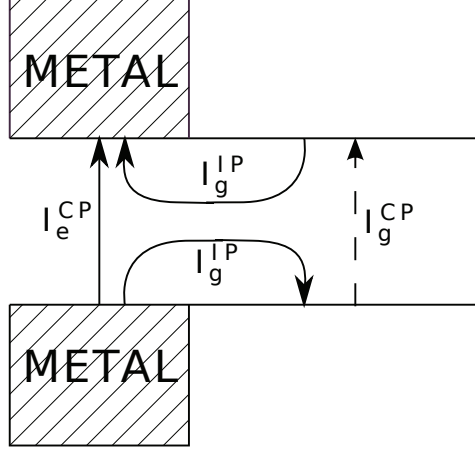


FIG. 2: Depiction of the currents in the MIEC. The superscript CP indicates cross-plane current and the superscript IP means in-plane currents. The subscript g indicates that the the flux is due to electrochemical reactions at the gas|ceria interface, while the subscript e is for electrode to electrode current. We notice we will have four currents: one, the cross-plane electron flux I_e^{CP} from the bottom to the top electrode, two the cross-plane ionic flux from top to bottom gas|ceria interface I_g^{CP} and the in-plane electronic fluxes I_g^{IP} from the gas|ceria interfaces to the electrodes.

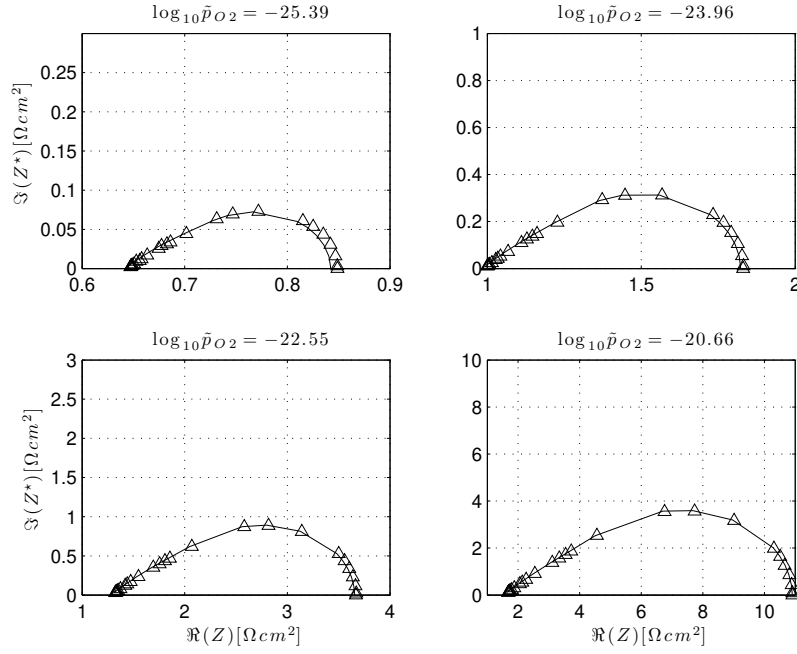


FIG. 3: The triangle indicated fitted computations while the solid line is the experimental value. The results are presented at $650^\circ C$ varying the \tilde{p}_{O_2} partial pressure.

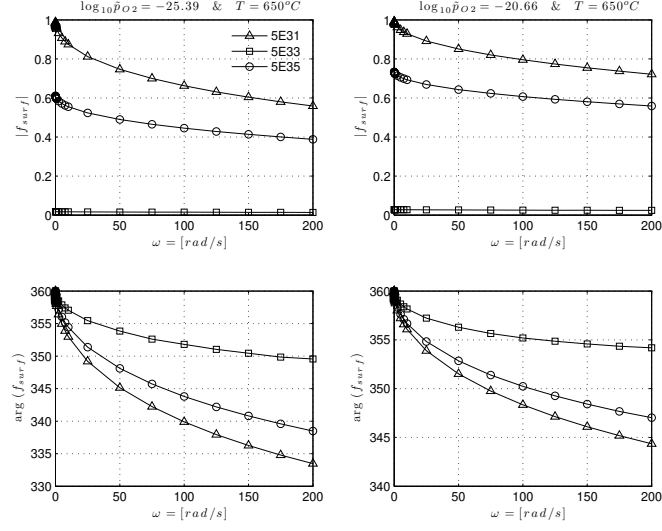


FIG. 4: Plot of $f_{surf} = \frac{R_{surf}}{R_{ion}^\perp}$ as a complex function of ω . We present two cases, both at 650°C , the one to the left at very reducing conditions $\tilde{p}_{O_2} = 10^{-25.32}$ and the one to the right at $\tilde{p}_{O_2} = 10^{-20.66}$, parametrized versus $\tilde{k}_f^{(0)}$.

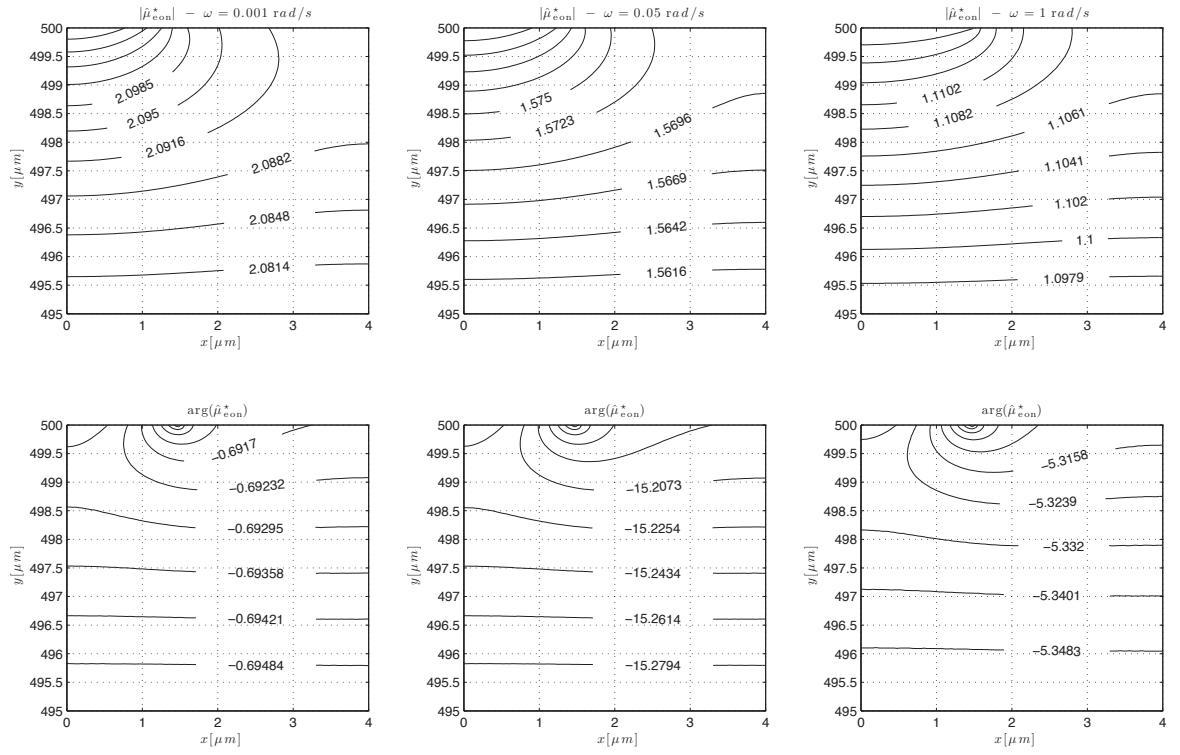


FIG. 5: Plots of the complex electrochemical potential of electrons $\hat{\mu}_{eon}(x, y, \omega)$ as a function of x and y in the case where $T = 650^\circ\text{C}$ and $\tilde{p}_{\text{O}_2} = 10^{-25}$. In the top panels we depict its absolute value $|\hat{\mu}_{eon}|$ while at the bottom we show its argument $\arg(\hat{\mu}_{eon})$. The applied frequency is increased from left to right, going from 0.001 rad/s to 1 rad/s.

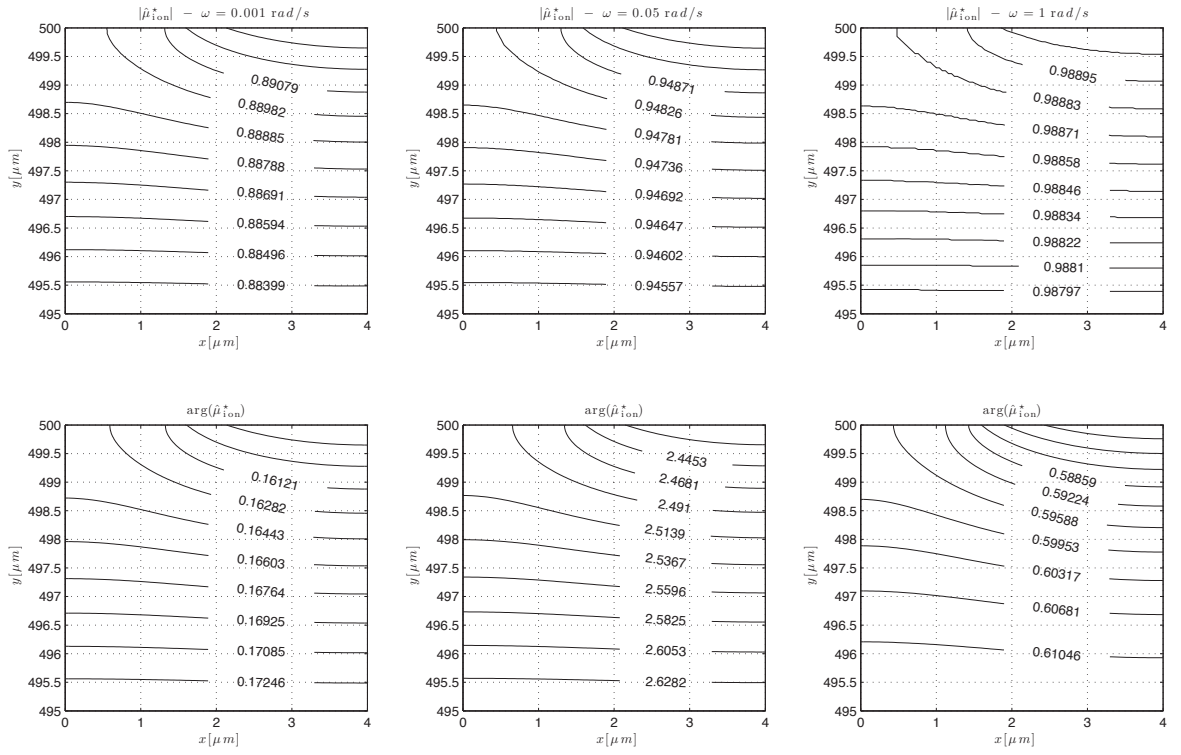


FIG. 6: Similar to Fig. 5, we depict the complex electrochemical potential of ions $\hat{\mu}_{ion}(x, y, \omega)$ where at the top we show $|\hat{\mu}_{ion}|$ and at the bottom $\arg(\hat{\mu}_{ion})$. The conditions are the same as Fig. 5 and so is the frequency range.

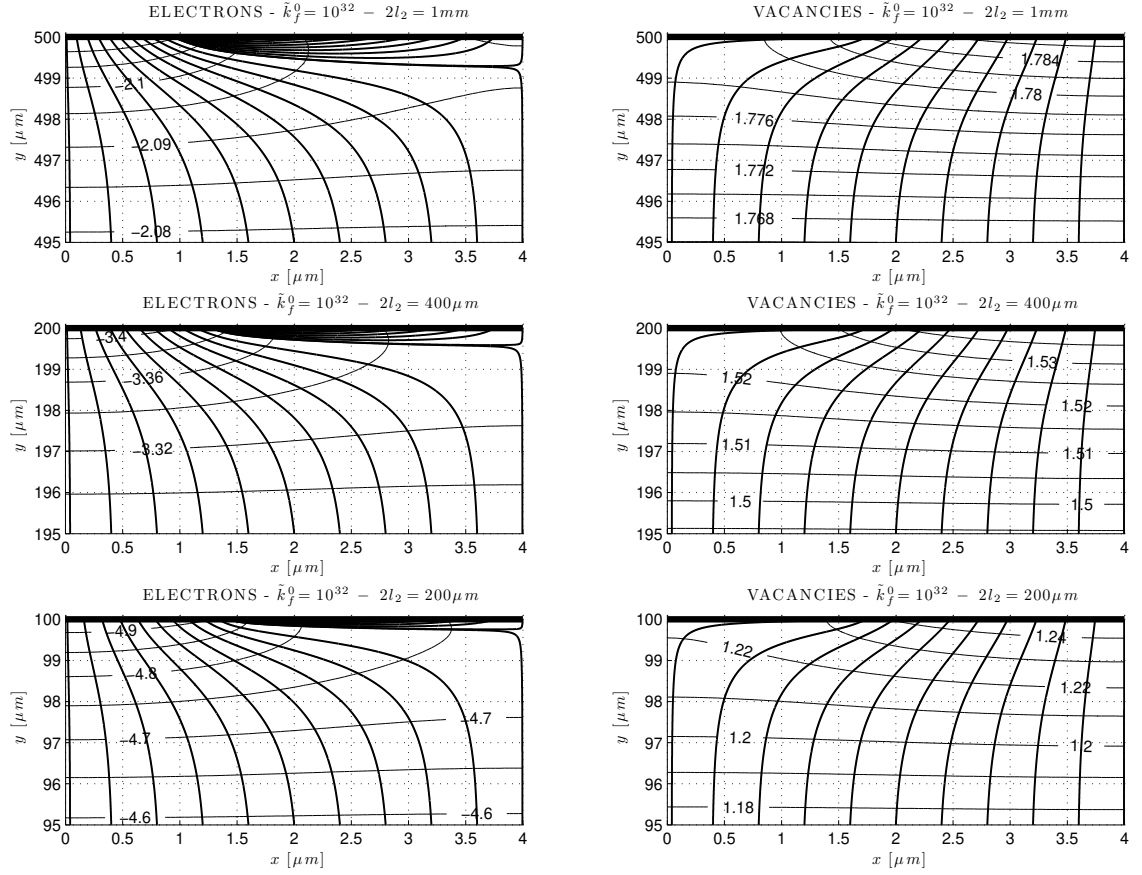


FIG. 7: . Results small bias excitation, i.e. impedance at $\omega = 0$, at $T = 650^\circ C$ and $\tilde{p}_{O_2} = 10^{-25.33}$. The $\hat{\mu}_{eon}$ (left column) and $\hat{\mu}_v$ (right column) along with their current lines are plotted. Each row corresponds to different thickness. As l_2 decreases (from top to bottom row) the area affected by surface reactions thins out; this phenomenon relates to an increase of the polarization resistance.

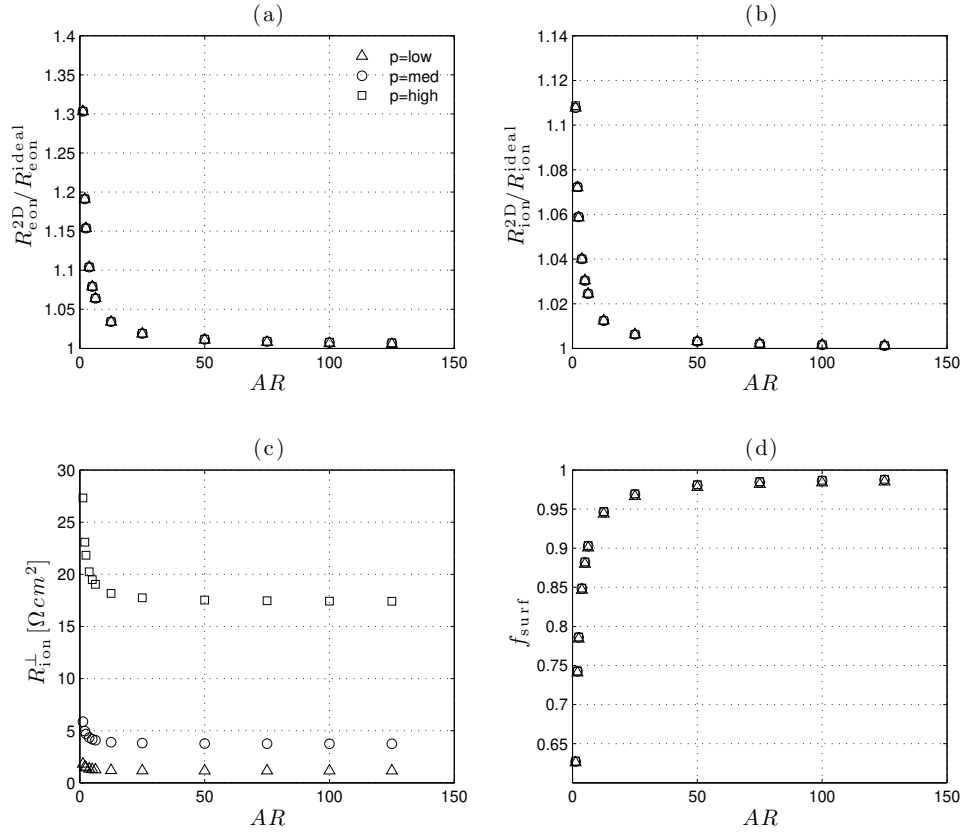


FIG. 8: Here it is shown the deviation of the 2D model from 1D behavior as a function of the aspect ratio $AR = (W_1 + W_2) / l_2$. We consider the case where $\tilde{k}_f^{(0)} = 10^{32}$, $T = 650^\circ C$ and we set $\tilde{p}_{O_2} = 10^{-25.32}$ ($p=low$), $\tilde{p}_{O_2} = 10^{-23.34}$ ($p=med$), $\tilde{p}_{O_2} = 10^{-20.66}$. The R_{eon}^{2D} and the R_{ion}^{2D} monotonically approach their 1D (ideal) value if AR is sufficiently large, and they surpass the ideal value if the AR is sufficiently small. Similarly the polarization resistance R_{ion}^{\perp} increases with decreasing the AR while the f_{surf} decreases, which indicates that if the thickness is reduced enough, the R_{ion}^{\perp} shifts from being surface dominated to being co-dominated by drift-diffusion.

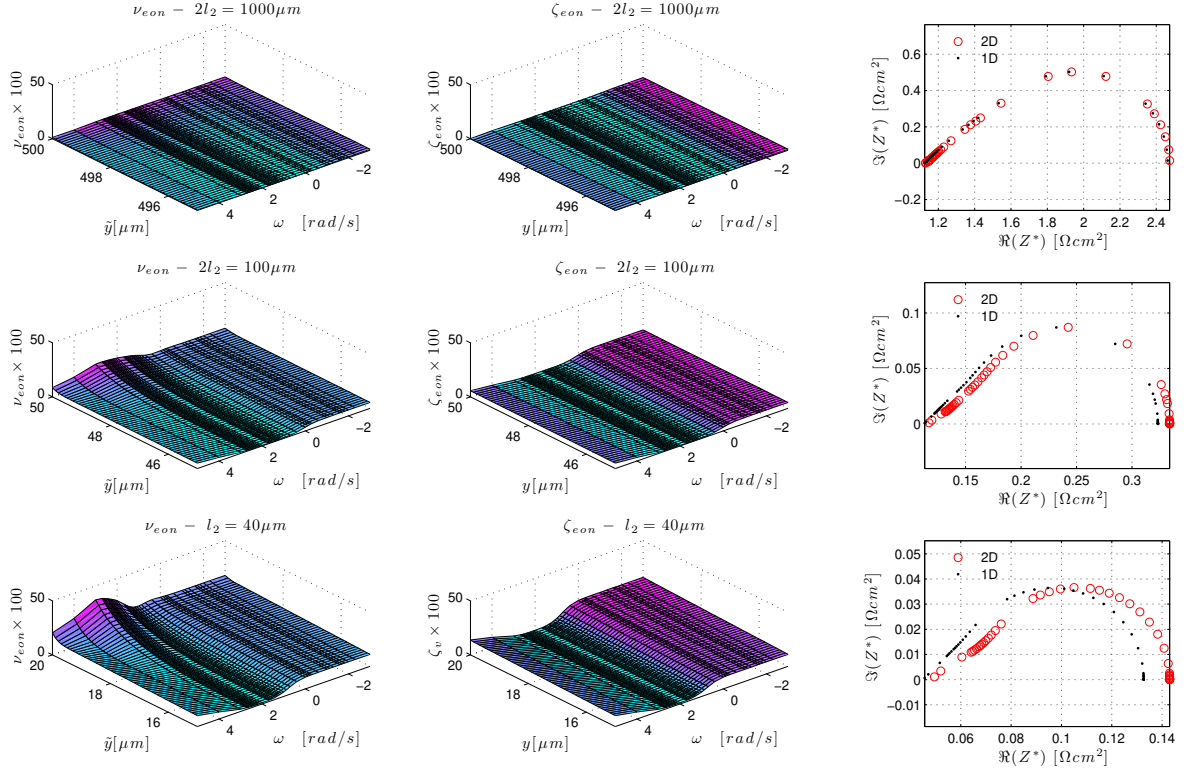


FIG. 9: Plots of the ν and ζ 's of the electrochemical potential of electrons (plots are shown up to $5\mu\text{m}$ from Γ_4 and Γ_5) as function of y and ω and of the impedance spectra as the aspect ratio changes (each line corresponds to a different aspect ratio, $2l_2 = 1000\mu\text{m}$, $2l_2 = 100\mu\text{m}$ and $2l_2 = 40\mu\text{m}$ correspond respectively to $AR = 125$, $AR = 12.5$ and $AR = 5$). A decrease of the aspect ratio corresponds to an increase of both ν and ζ and an increase between the (ideal) 1D impedance and the 2D impedance spectra.

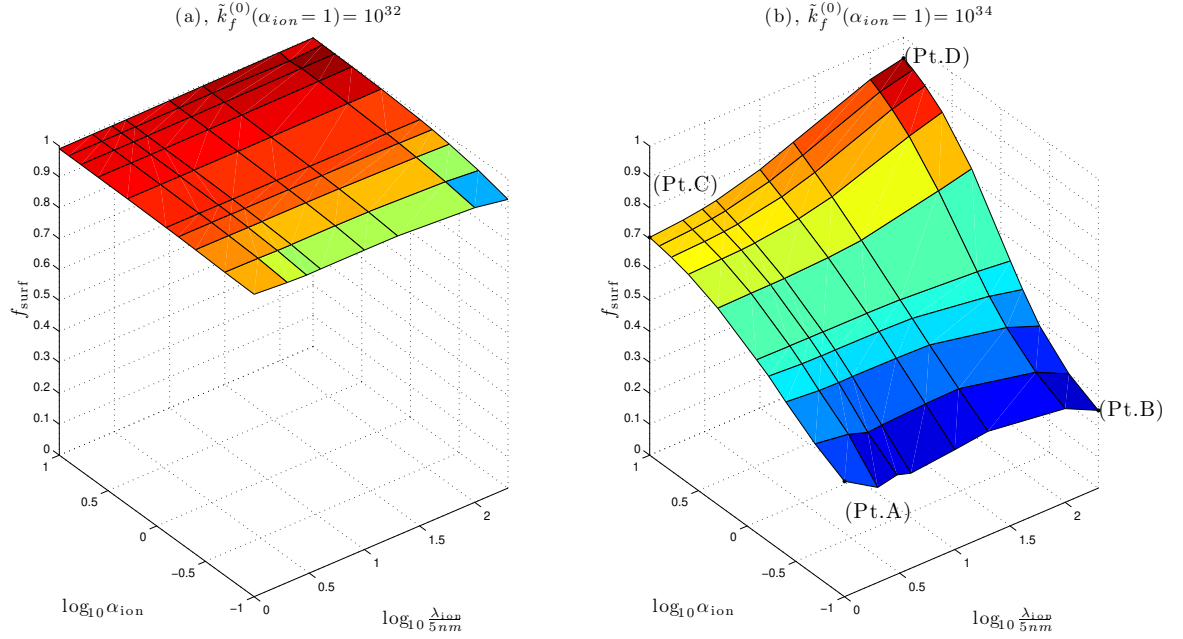


FIG. 10: Depiction of f_{surf} in the case $T = 650^\circ C$ and $\tilde{p}_{O_2} = 10^{-25.32}$ as a function of the ratio between near interface and bulk diffusivity, $\alpha_{ion} = D_{ion}^{SURF}/D_{ion}^{BULK}$ and $\alpha_{eon} = D_{eon}^{SURF}/D_{eon}^{BULK}$ ($\alpha_{ion} = \alpha_{eon}$), and length scale of the diffusive gradient $\lambda_{ion} = \lambda_{eon}$, for $k_f^{(0)} = 10^{32}$ (left panel) and $k_f^{(0)} = 10^{34}$ (right panel).

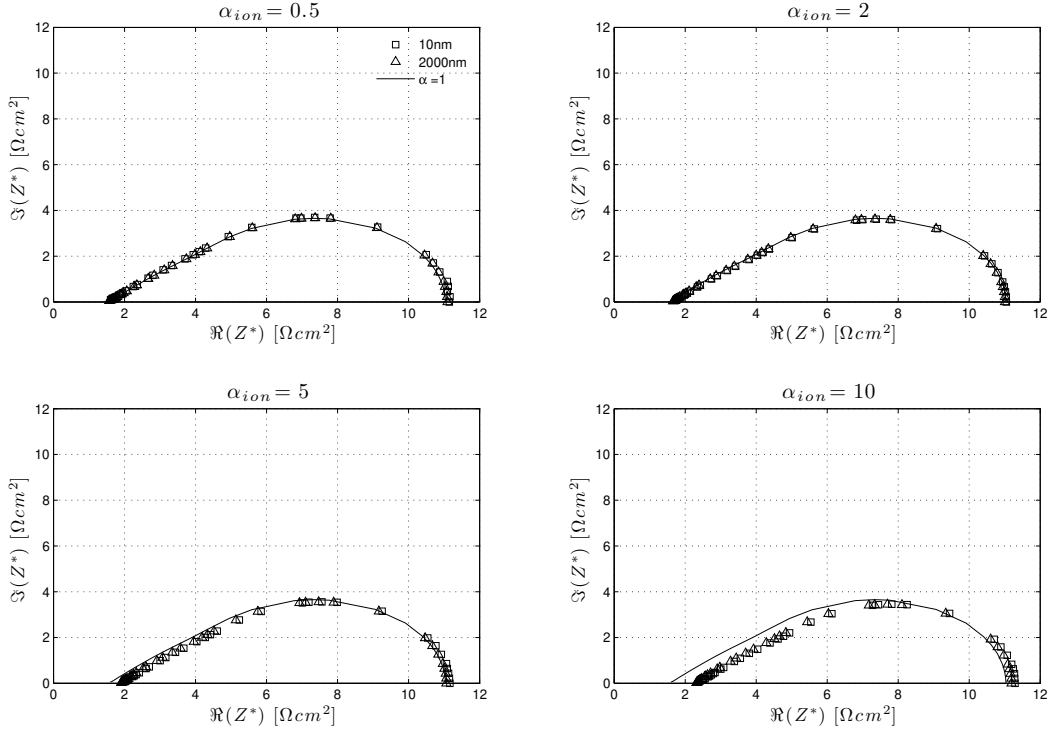


FIG. 11: Impedance of the sample under the conditions: $\tilde{k}_f^{(0)} = 10^{32}$, $\tilde{p}_{O_2} = 10^{-25.33}$ and $T = 650^\circ C$, where $\alpha_{eon} = \alpha_{ion}$ ($\alpha_m = D_m^{\text{SURF}}/D_m^{\text{BULK}}$) and $\lambda_{ion} = \lambda_{eon}$. The solid line represents the case where $\alpha_{ion} = 1$, the triangles and the squares indicate respectively $\lambda_{ion} = 5nm$ and $\lambda_{ion} = 1\mu m$. Each panel corresponds to a different value of α_{ion} . We notice small deviations from the case $\alpha_{ion} = 1$